

1N119WS

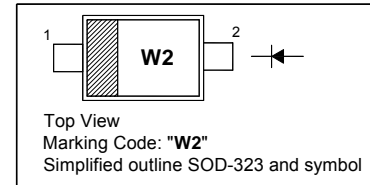
Silicon Epitaxial Planar Switching Diode

Applications

- High speed switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

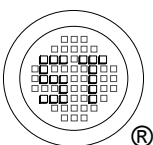


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Peak Forward Current	I_{FM}	300	mA
Non-repetitive Peak Surge Forward Current ($t = 1\text{ }\mu\text{s}$)	I_{FSM}	4	A
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$ at $I_F = 100\text{ mA}$	V_F	0.8 1.2	V
Reverse Current at $V_R = 80\text{ V}$	I_R	0.1	μA
Capacitance between Terminals at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	2	pF
Reverse Recovery Time at $V_R = 6\text{ V}$, $I_F = 10\text{ mA}$, $R_L = 50\text{ }\Omega$	t_{rr}	3	ns



SEMTECH ELECTRONICS LTD.
Subsidiary of Sino-Tech International (BVI) Limited



Dated : 15/06/2009

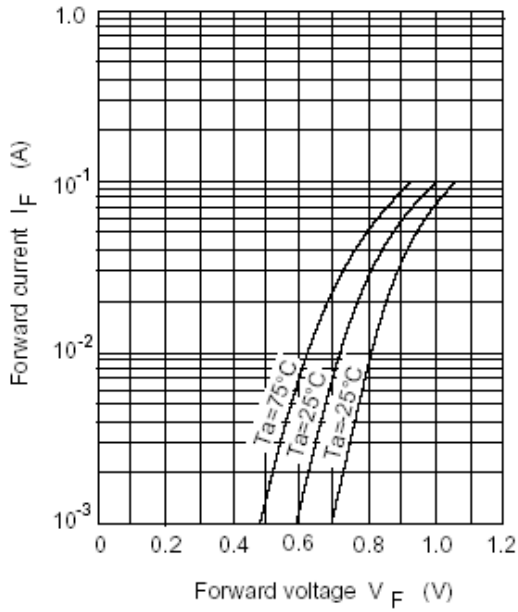


Fig.1 Forward current Vs. Forward voltage

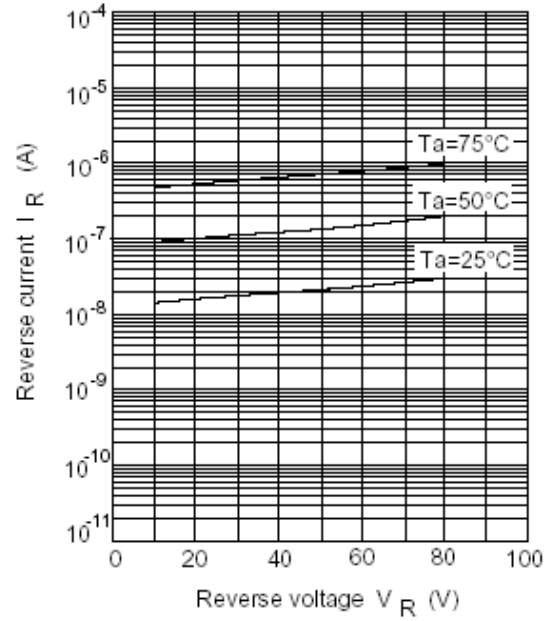


Fig.2 Reverse current Vs. Reverse voltage

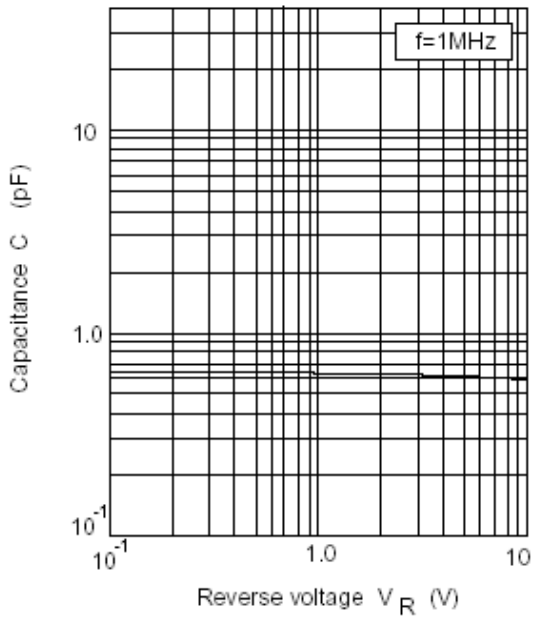
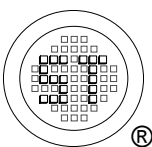


Fig.3 Capacitance Vs. Reverse voltage



SEMTECH ELECTRONICS LTD.
Subsidiary of Sino-Tech International (BVI) Limited

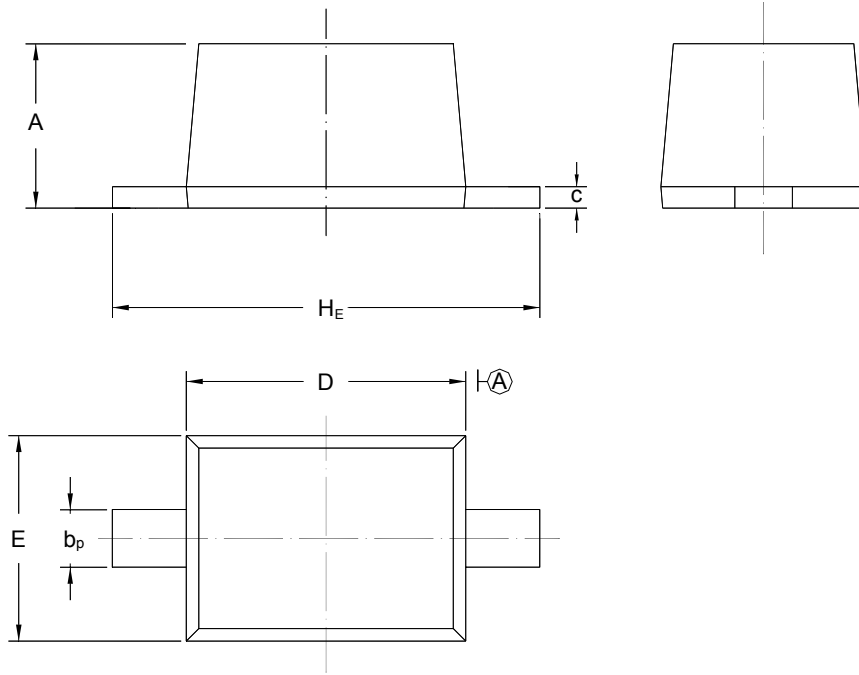


1N119WS

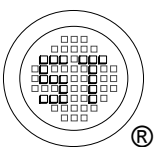
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b_p	C	D	E	H_E
mm	1.10 0.80	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30



SEMTECH ELECTRONICS LTD.
Subsidiary of Sino-Tech International (BVI) Limited



Dated : 15/06/2009